

AD-A191 984 X-Y-THETA-Z STAGE FOR MASKED ION BEAM LITHOGRAPHY(U)
NAVAL OCEAN SYSTEMS CENTER SAN DIEGO CA
J M REEDS ET AL. MAY 87

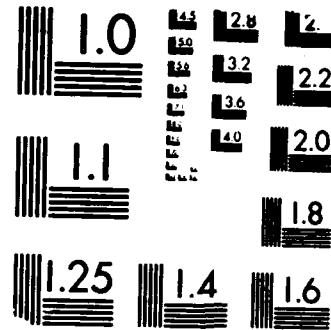
1/1

UNCLASSIFIED

F/G 13/8

NL





MICROCOPY RESOLUTION TEST CHART
MIREAU STANDARDS 1963 A

AD-A191 904

UNCLAS
SECURITY

REPORT DOCUMENTATION PAGE

TMG FILE COPY

1a. REPORT SECURITY CLASSIFICATION UNCLASSIFIED		1b. RESTRICTIVE MARKINGS					
2a. SECURITY CLASSIFICATION AUTHORITY		3. DISTRIBUTION/AVAILABILITY OF REPORT Approved for public release; distribution is unlimited.					
2b. DECLASSIFICATION/DOWNGRADING SCHEDULE		4. PERFORMING ORGANIZATION REPORT NUMBER(S)					
5a. NAME OF PERFORMING ORGANIZATION Naval Ocean Systems Center	5b. OFFICE SYMBOL <i>(if applicable)</i>	6. MONITORING ORGANIZATION REPORT NUMBER(S) DTIC ELECTED S MAR 1 1 1988 D					
6c. ADDRESS (City, State and ZIP Code) San Diego, CA 92152-5000		7b. ADDRESS (City, State and ZIP Code)					
8a. NAME OF FUNDING/SPONSORING ORGANIZATION Naval Air Systems Command	8b. OFFICE SYMBOL <i>(if applicable)</i> NAVAIR	9. PROCUREMENT INSTRUMENT IDENTIFICATION NUMBER					
8c. ADDRESS (City, State and ZIP Code) Washington, DC 20361		10. SOURCE OF FUNDING NUMBERS <table border="1"><tr><td>PROGRAM ELEMENT NO. 78011N</td><td>PROJECT NO. ET50</td><td>TASK NO. R1050</td><td>AGENCY ACCESSION NO. DN388 597</td></tr></table>		PROGRAM ELEMENT NO. 78011N	PROJECT NO. ET50	TASK NO. R1050	AGENCY ACCESSION NO. DN388 597
PROGRAM ELEMENT NO. 78011N	PROJECT NO. ET50	TASK NO. R1050	AGENCY ACCESSION NO. DN388 597				
11. TITLE (Include Security Classification) X-Y-O-Z Stage for Masked Ion Beam Lithography							
12. PERSONAL AUTHOR(S) I. Lagnado							
13a. TYPE OF REPORT Journal Article	13b. TIME COVERED FROM _____ TO _____	14. DATE OF REPORT (Year, Month, Day) May 1987	15. PAGE COUNT				
16. SUPPLEMENTARY NOTATION							
17. COSATI CODES		18. SUBJECT TERMS (Continue on reverse if necessary and identify by block number)					
FIELD	GROUP	SUB-GROUP					
19. ABSTRACT (Continue on reverse if necessary and identify by block number) <p>A mechanical stage and electronic drive servos have been built which provide six degrees of freedom of motion in positioning. The stage is used in conjunction with a mask-wafer alignment sensing system to align a semiconductor wafer with a mask to 0.1 micrometer tolerance in a masked ion beam exposure system. Because the exposure system utilizes a step and repeat mode of operation, the stage system was designed to operate at high speed to achieve high wafer throughput. A backlash free capstan drive system is used on the X, Y, and Z servos to achieve the high precision, high speed performance.</p> <p>The wafer to be exposed is mounted on top of an X-Y stage, which is, in turn, mounted on a rotary (θ) stage, which is then mounted on a platform. The platform is supported from a base by three deformable diaphragms which allow limited vertical (Z) or tilt motion of the entire stage assembly. In step and repeat operation, the X and Y motions are relatively large from the chip-to-chip, while the θ and Z motions are very small. Mounting the X-Y stage on the top of the stage assembly provides the design with the lowest mass to be accelerated in stepping, and has the additional advantage that the algorithms for providing mask-wafer alignment error signals remain the same no matter where the chip being aligned is located on the wafer. Dedicated microprocessors for each of the X, Y, and θ axes, incorporating digital error integration, provide the required precision of motion.</p>							
20. DISTRIBUTION/AVAILABILITY OF ABSTRACT <input type="checkbox"/> UNCLASSIFIED/UNLIMITED <input checked="" type="checkbox"/> SAME AS RPT <input type="checkbox"/> DTIC USERS		21. ABSTRACT SECURITY CLASSIFICATION UNCLASSIFIED					
22a. NAME OF RESPONSIBLE INDIVIDUAL I. Lagnado		22b. TELEPHONE (Include Area Code) 619-225-6735	22c. OFFICE SYMBOL Code 5503				

DD FORM 1473, 84 JAN

83 APR EDITION MAY BE USED UNTIL EXHAUSTED
ALL OTHER EDITIONS ARE OBSOLETE

UNCLASSIFIED
SECURITY CLASSIFICATION OF THIS PAGE

for
I

ed
tion

X-Y-θ-Z STAGE FOR MASKED ION BEAM LITHOGRAPHY

J.W. Reeds, D.V. Lilly, H. McNulty, and G.M. Thorne-Booth

Hughes Research Laboratories
3011 Malibu Canyon Road
Malibu, CA 90265

by	
Distribution/	
Availability Codes	
Dist	Avail and/or Special
A-1	

ABSTRACT



A mechanical stage and electronic drive servos have been built which provide six degrees of freedom of motion in positioning. The stage is used in conjunction with a mask-wafer alignment sensing system to align a semiconductor wafer with a mask to 0.1 micrometer tolerances in a masked ion beam exposure system. Because the exposure system utilizes a step and repeat mode of operation, the stage system was designed to operate at high speed to achieve high wafer throughput. A backlash free capstan drive system is used on the X, Y, and θ servos to achieve the high precision, high speed performance.

The wafer to be exposed is mounted on top of an X-Y stage, which is, in turn, mounted on a rotary (θ) stage, which is then mounted on a platform. The platform is supported from a base by three deformable diaphragms which allow limited vertical (Z) or tilt motion of the entire stage assembly. In step and repeat operation, the X and Y motions are relatively large from chip to chip, while the θ and Z motions are very small. Mounting the X-Y stage on the top of the stage assembly provides the design with the lowest mass to be accelerated in stepping, and has the additional advantage that the algorithms for providing mask-wafer alignment error signals remain the same no matter where the chip being aligned is located on the wafer. Dedicated microprocessors for each of the X, Y, and θ axes, incorporating digital error integration, provide the required precision of motion.

END
DATE
FILMED

6-1988

DTIC